

Features

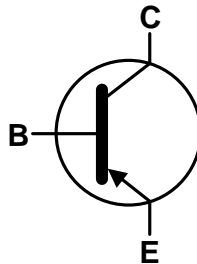
- $BV_{CEO} > -60V$
- $I_C = -600mA$ Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMST2222A
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

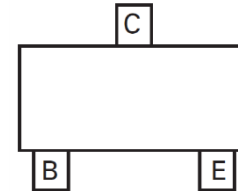
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (Approximate)



Top View



Device Symbol



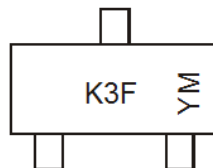
Pin-out Top View

Ordering Information (Notes 4 & 5)

Product	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMST2907A-7-F	NRND	AEC-Q101	K3F	7	8	3,000
MMST2907A-7	Active	AEC-Q101	K3F	7	8	3,000
MMST2907AQ-7	Active	Automotive	K3F	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
 5. NRND = Not Recommended for New Design. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



K3F = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: A = 2013)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	
Code	X	Y	Z	A	B	C	D	E	F	G	H	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes: 6. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

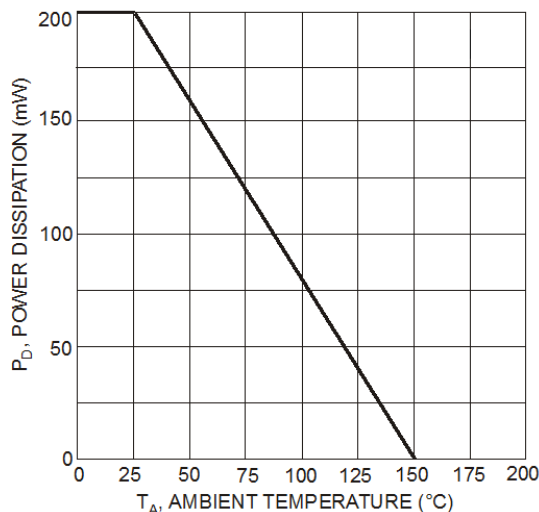
Thermal Characteristics and Derating Information


Fig. 1 Max Power Dissipation vs. Ambient Temperature

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					
Collector-Base Breakdown Voltage	BV _{CBO}	-60	—	V	I _C = -10μA, I _E = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-60	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—	V	I _E = -10μA, I _C = 0
Collector Base Cutoff Current	I _{CBO}	—	-10	nA μA	V _{CB} = -50V, I _E = 0 V _{CB} = -50V, I _E = 0, T _A = +125°C
Collector Cutoff Current	I _{CEX}	—	-50	nA	V _{CE} = -30V, V _{EB(OF F)} = -0.5V
Base Cutoff Current	I _{BL}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -0.5V
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h _{FE}	75 100 100 100 50	— — — 300 —	—	I _C = -100μA, V _{CE} = -10V I _C = -1mA, V _{CE} = -10V I _C = -10mA, V _{CE} = -10V I _C = -150mA, V _{CE} = -10V I _C = -500mA, V _{CE} = -10V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	-0.4 -1.6	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	1.3 2.6	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	8	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	30	pF	V _{EB} = -2V, f = 1.0MHz, I _C = 0
Current Gain-Bandwidth Product	f _T	200	—	MHz	V _{CE} = -20V, I _C = -50mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t _{on}	—	45	ns	V _{CC} = -30V, I _C = -150mA, I _{B1} = -15mA
Delay Time	t _d	—	10	ns	
Rise Time	t _r	—	40	ns	
Turn-Off Time	t _{off}	—	100	ns	V _{CC} = -6V, I _C = -150mA, I _{B1} = I _{B2} = -15mA
Storage Time	t _s	—	80	ns	
Fall Time	t _f	—	30	ns	

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

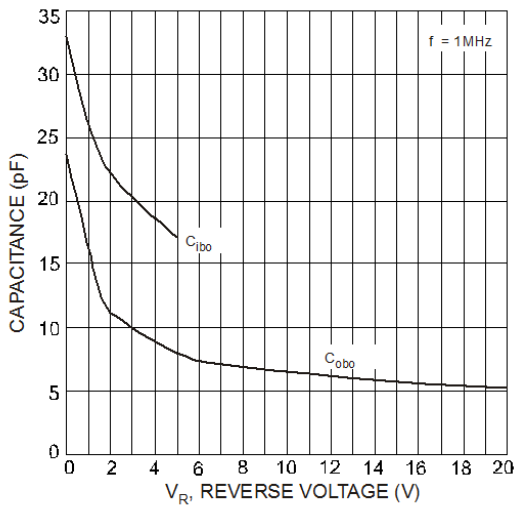


Fig. 2 Typical Capacitance Characteristics

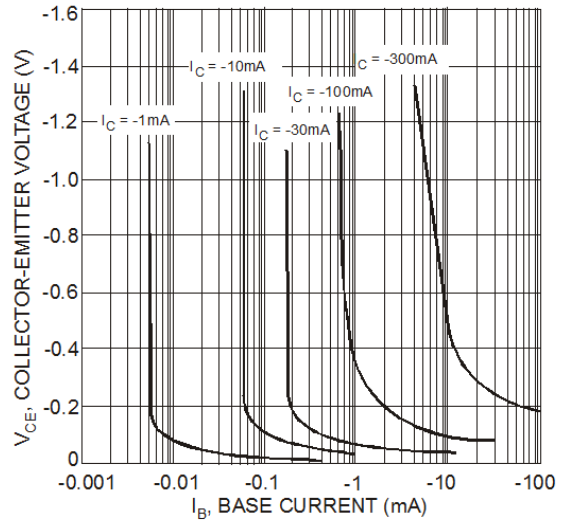


Fig. 3 Typical Collector Saturation Region

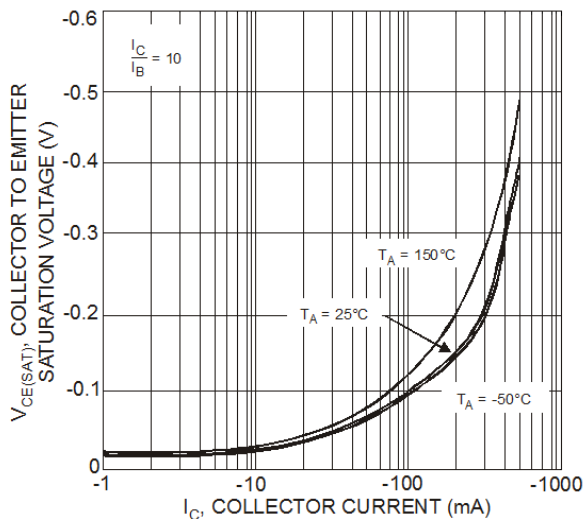


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

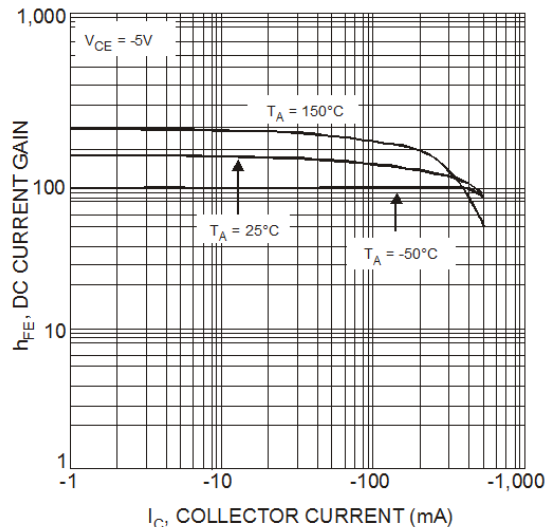


Fig. 5 DC Current Gain vs. Collector Current

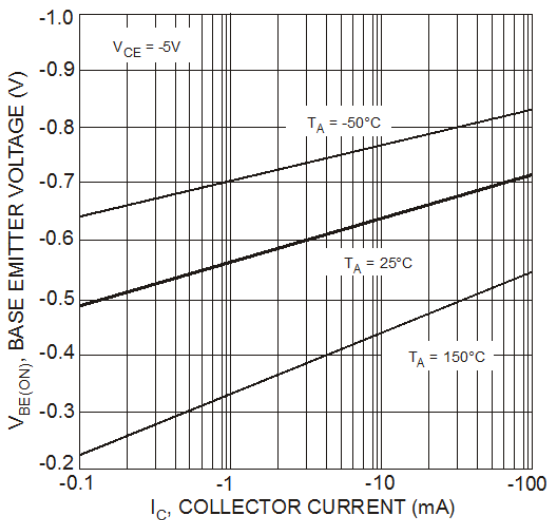


Fig. 6 Base-Emitter Voltage vs. Collector Current

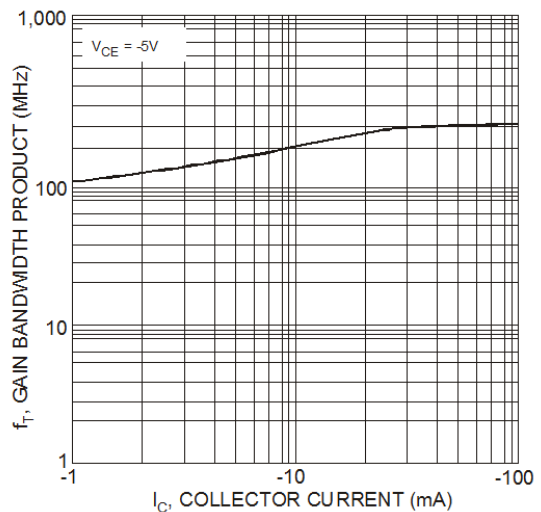
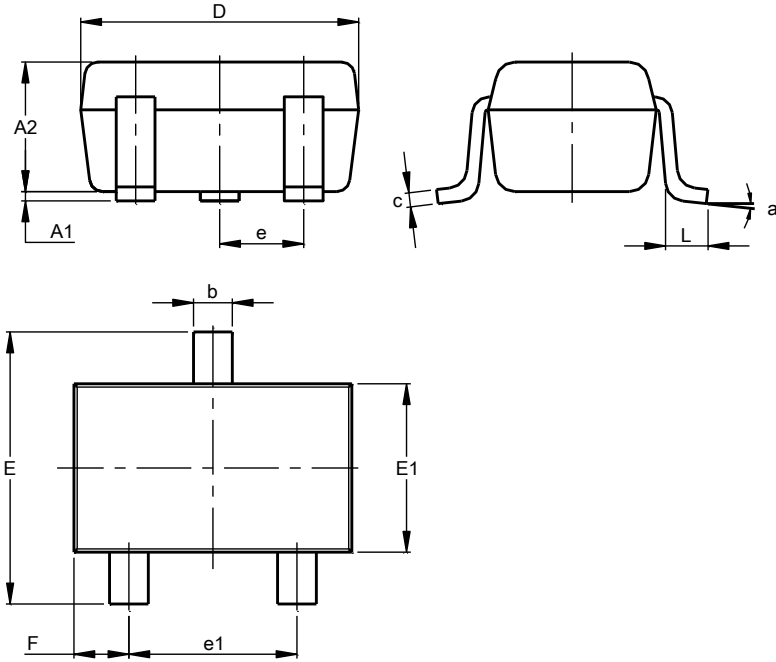


Fig. 7 Gain Bandwidth Product vs. Collector Current

Package Outline Dimensions

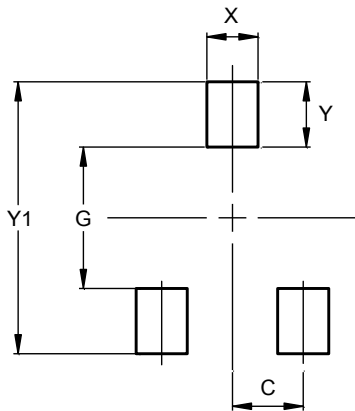
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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